Electronic Devices

Final Term Lecture - 07

Reference book:

Electronic Devices and Circuit Theory (Chapter-7)

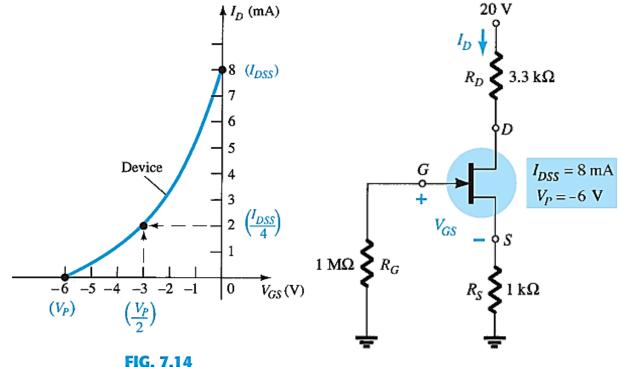
Robert L. Boylestad and L. Nashelsky, (11th Edition)



SELF-BIAS EXAMPLE Contd.

• Plot the transfer curve using I_{DSS} and V_P using shorthand method:

V _{GS}	l _D
0	I _{DSS}
0.3V _P	I _{DSS} /2
0.5V _P	I _{DSS} /4
V _P	0mA



Sketching the device characteristics for the JFET of Fig. 7.12.

FIG. 7.12 *Example 7.2.*

SELF-BIAS EXAMPLE Contd.

Superimpose the load line on top of the transfer curve:

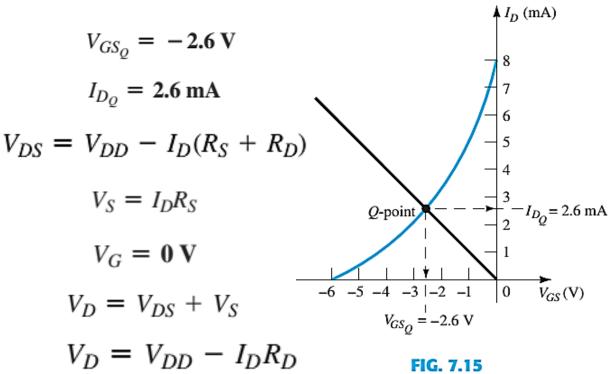


FIG. 7.15

Determining the Q-point for the network of Fig. 7.12.

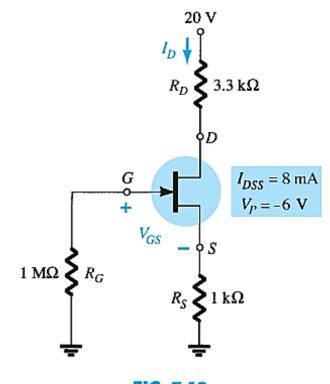


FIG. 7.12 Example 7.2.

JFET: VOLTAGE-DIVIDER BIAS

- The source V_{DD} was separated into two equivalent sources to permit a further separation of the input and output regions of the network.
- Since $I_G = 0A$, Kirchoff's current law requires that $I_{R1} = I_{R2}$ and the series equivalent circuit appearing to the left of the figure can be used to find the level of V_G .

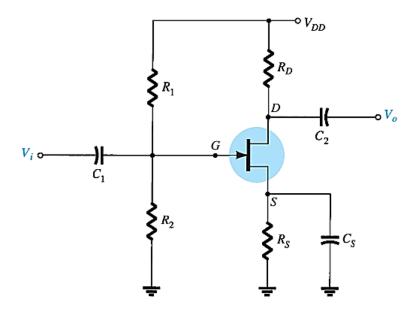


FIG. 7.17
Voltage-divider bias arrangement.

VOLTAGE-DIVIDER BIAS

V_G can be found using the voltage divider rule:

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2}$$

Using Kirchoff's Law on the input loop:

$$V_D = V_{DD} - I_D R_D$$

$$|V_D| = V_{DD} - I_D R_D |V_{DS}| = V_{DD} - I_D (R_D + R_S)$$

$$V_S = I_D R_S$$

$$V_{GS} = V_G - I_D R_S$$

Rearranging and using $I_D = I_S$:

$$I_{R1} = I_{R2} = \frac{V_{DD}}{R_1 + R_2}$$

 Again the Q point needs to be established by plotting a line that intersects the transfer curve.

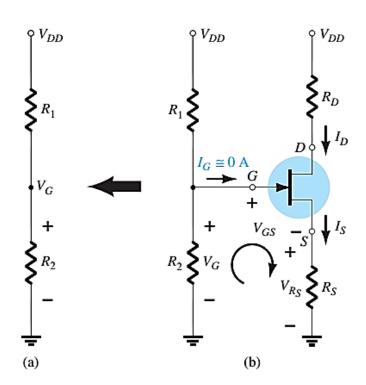


FIG. 7.18 Redrawn network of Fig. 7.17 for dc analysis.

VOLTAGE-DIVIDER BIAS

- Graphical Approach (to find V_{GSQ} and I_{DQ}):
 - Plot a line for:

$$V_{GS} = V_{G}$$
 when $I_{D} = 0$ A

$$V_{GS} = 0V$$
 when $I_D = V_G/R_S$.

Plot the transfer curve using I_{DSS} and V_P using shorthand method.

The Q-point is located at the intersection.

V _{GS}	l _D
0	I _{DSS}
0.3V _P	I _{DSS} /2
0.5V _P	I _{DSS} /4
V _P	0mA

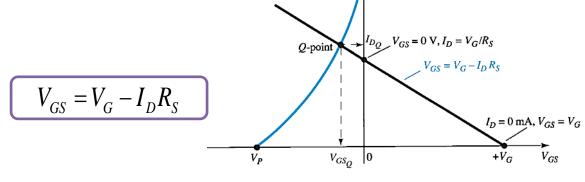


FIG. 7.19

Sketching the network equation for the voltage-divider configuration.

EFFECT OF INCREASING VALUES OF R_S

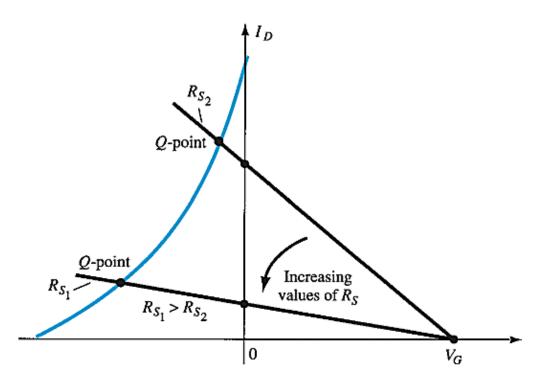


FIG. 7.20 Effect of R_S on the resulting Q-point.

JFET: VOLTAGE-DIVIDER BIAS EXAMPLE

• Determine I_{DQ} , V_{GSQ} , V_D , V_S , V_{DS} and V_{DG} .

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2} \quad \boxed{V}$$

$$V_{GS} = V_G - I_D R_S$$

$$V_{DS} = V_{DD} - I_D(R_D + R_S)$$

$$V_{GSO} = -1.8V$$

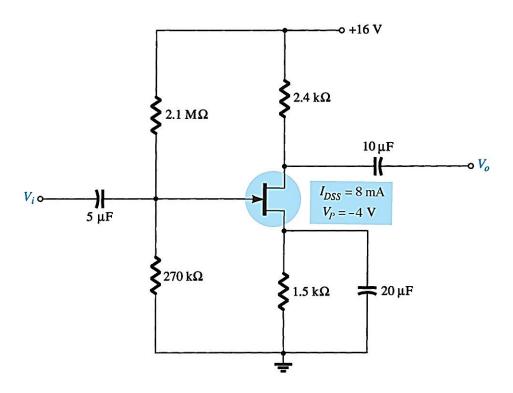
$$I_{DQ} = 2.4mA$$

$$V_D = 10.24V$$

$$V_{s} = 3.6V$$

$$V_{DS} = 6.64V$$

$$V_{DG} = 8.24V$$



VOLTAGE-DIVIDER BIAS EXAMPLE Contd.

- Graphical Approach (to find V_{GSQ} and I_{DQ}):
 - Plot a line for:

$$V_{GS} = V_{G}$$
 when $I_{D} = 0A$
 $V_{GS} = 0V$ when $I_{D} = V_{G}/R_{S}$.

- Plot the transfer curve using I_{DSS} and V_P using shorthand method.
- Identify the Q-point.

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2}$$

$$V_{GS} = V_G - I_D R_S$$

$$V_D = V_{DD} - I_D R_D$$

$$V_S = I_D R_S$$

$$V_{DS} = V_{DD} - I_D(R_D + R_S)$$

$$V_{DS} = V_D - V_S$$

$$V_{DG} = V_D - V_G$$

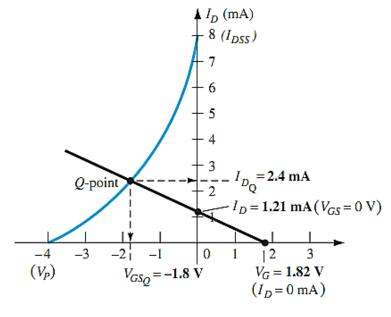


FIG. 7.22

Determining the Q-point for the network of Fig. 7.21.

D-MOSFET SELF-BIAS

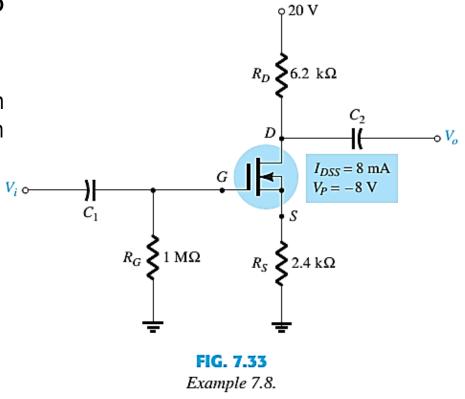
• D-MOSFET bias circuits are **similar to JFETs**.

The only difference is that D-MOSFETs can operate with positive values of V_{GS} and with I_D values that exceed I_{DSS}.

$$I_G \approx 0A$$

$$I_D = I_S$$

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

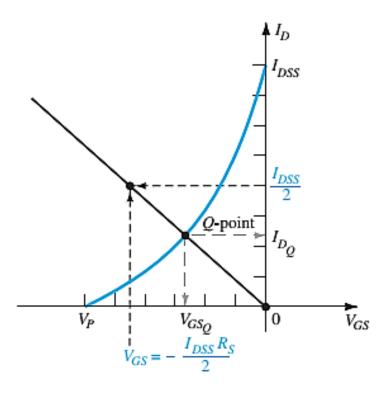


D-MOSFET SELF-BIAS

- Graphical Approach (to find V_{GSQ} and I_{DQ}):
 - Plot the *transfer curve* using I_{DSS} and V_P using *shorthand method*.
 - Plot I_D vs V_{GS} using $V_{GS} = -I_D R_S$.
 - ullet Take a positive value of $oldsymbol{V_{GS}}$ and find the $oldsymbol{I_D}$ value using

$$I_D = I_{DSS} (1 - \frac{V_{GS}}{V_P})^2$$

• The Q-point is located at the intersection.

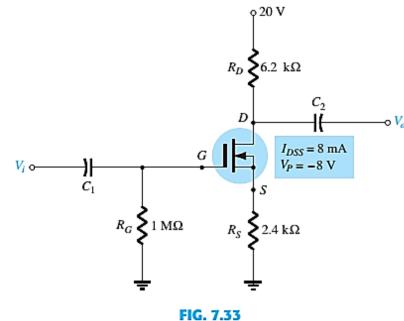


D-MOSFET SELF-BIAS EXAMPLE

- Determine the I_{DQ}, V_{GSQ} and V_D.
- Graphical Approach (to find V_{GSQ} and I_{DQ}):
 - Plot the transfer curve using I_{DSS} and V_P using shorthand method.
 - Take a positive value of V_{GS} and find the I_D value using

$$I_D = I_{DSS} (1 - \frac{V_{GS}}{V_P})^2$$

- Plot I_D vs V_{GS} using $V_{GS} = -I_D R_S$.
- Identify the intersection Q-point.



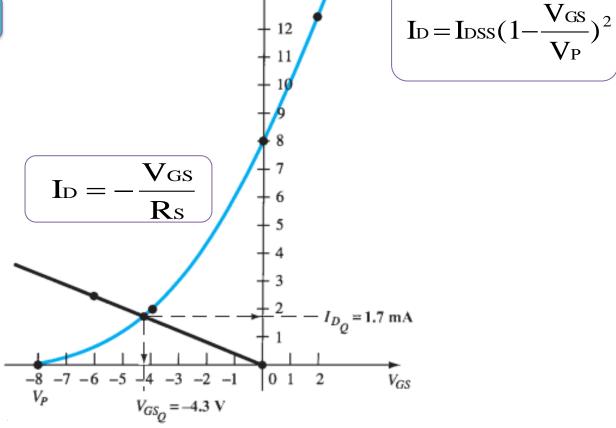
D-MOSFET SELF-BIAS EXAMPLE



$$V_{GSQ} = -4.3 V$$

$$I_{DQ} = 1.7 \text{ mA}$$

$$V_D = 9.46 \text{ V}$$



 I_D (mA)

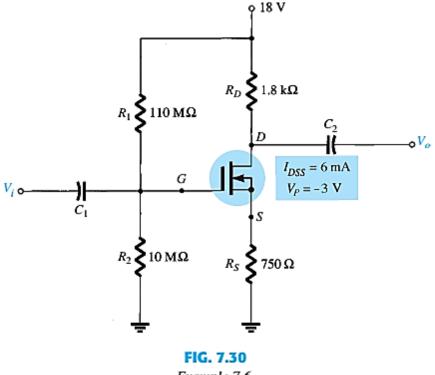


D-MOSFET VOLTAGE-DIVIDER BIAS

D-MOSFET bias circuits are similar to JFETs.

$$I_{G} \approx 0A \qquad I_{D} = I_{S}$$

$$I_{D} = I_{DSS} (1 - \frac{V_{GS}}{V_{P}})^{2}$$



D-MOSFET VOLTAGE-DIVIDER BIAS

- Graphical Approach (to find V_{GSQ} and I_{DQ}):
 - Plot the transfer curve using I_{DSS} and V_P using shorthand method.
 - Take a positive value of V_{GS} and find the I_D value using

$$I_D = I_{DSS} (1 - \frac{V_{GS}}{V_P})^2$$

- Plot I_D vs V_{GS} using $V_{GS} = V_G I_D R_S$.
- The Q-point is located at the intersection.

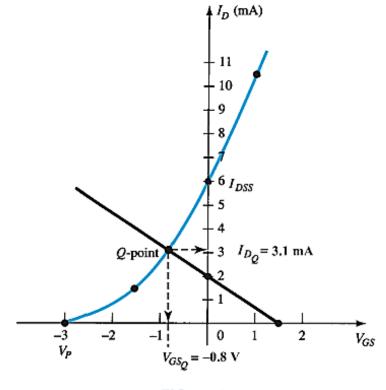


FIG. 7.31

Determining the Q-point for the network of Fig. 7.30.

End of Lecture-7